

No.4113

2SK1747

N-Channel Junction Silicon FET

SANYOHF amplifiers low frequency amplifiers
analog switches**Features**

- The 2SK1747 is formed with two chips, being equivalent to the 2SK937 placed in one package.
- Excellent in thermal equilibrium, pair capability and suitable for use in differential amp.
- Adoption of FBET process.

Absolute Maximum Ratings at Ta = 25°C

Drain to Source Voltage	V _{DSX}	40	V
Gate to Drain Voltage	V _{GDS}	-40	V
Gate Current	I _G	10	mA
Drain Current	I _D	75	mA
Allowable Power Dissipation	P _D	250	mW
Total Dissipation	P _T	400	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

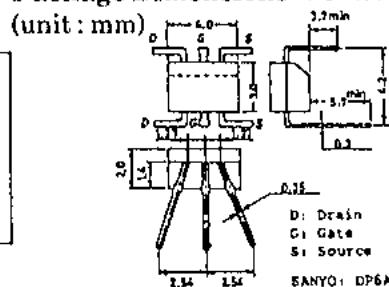
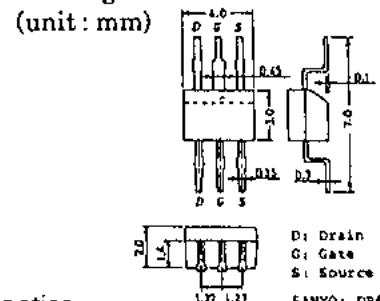
Electrical Characteristics at Ta = 25°C

		min	typ	max	unit
G-D Breakdown Voltage	V _{(BR)GDS}	-40			V
Gate to Source Leakage Current	I _{GSS}			-1.0	nA
Cutoff Voltage	V _{GSOFF}	-2.0	-3.0	-5.0	V
Cutoff Voltage Ratio	V _{GSOFF} (small/large)	0.85			
Drain Current	I _{DSS*}	40	75	mA	
Drain Current Ratio	V _{DS} = 10V, I _{DSS} (small/large)	0.85			
Forward Transfer Admittance	Y _{fs} (1)	10	15		mS
	Y _{fs} (2)	22	30		mS
Forward Transfer Admittance Ratio	Y _{fs} (small/large)	0.85			
Input Capacitance	C _{iss}	11			pF
Reverse Transfer Capacitance	C _{rss}	2.5			pF
Noise Figure	NF	1.5			dB
Static Drain to Source on State Resistance	R _{DS(on)}	30			Ω

* : Pulse Test Pulse Width \leq 2ms.※ : The 2SK1747 is classified by I_{DSS} as follows (unit : mA)

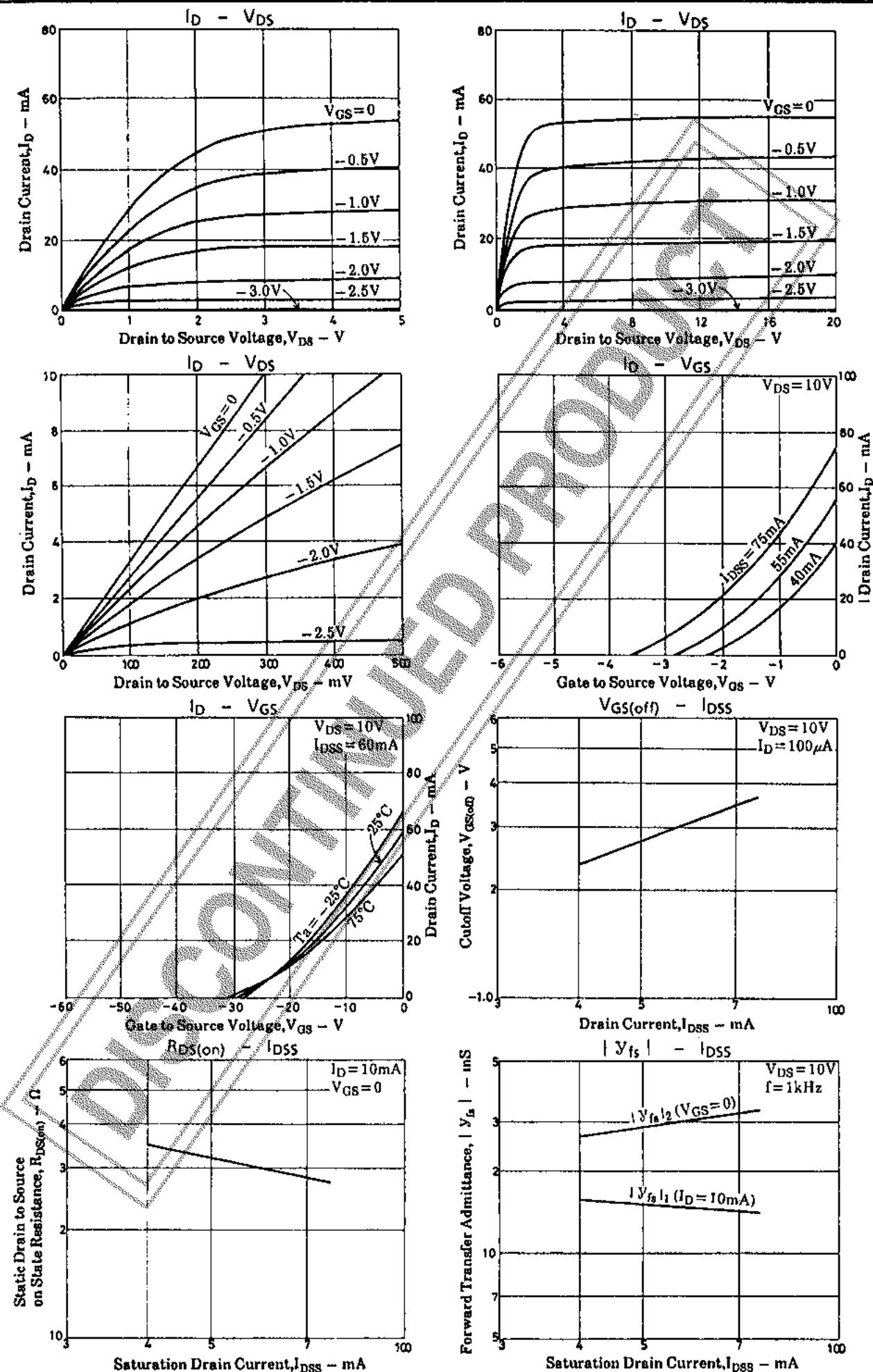
40	3	52	48	4	63	57	5	75
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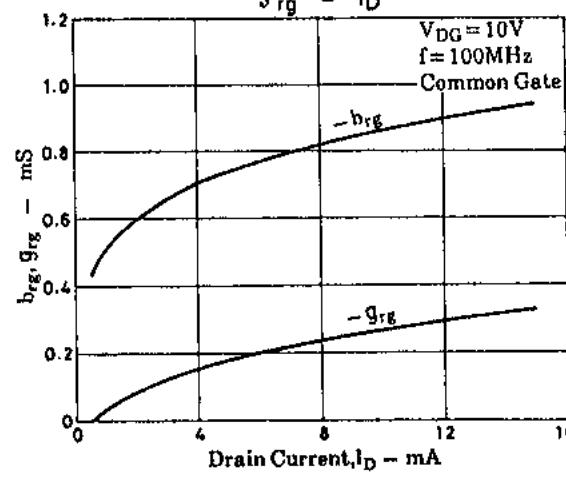
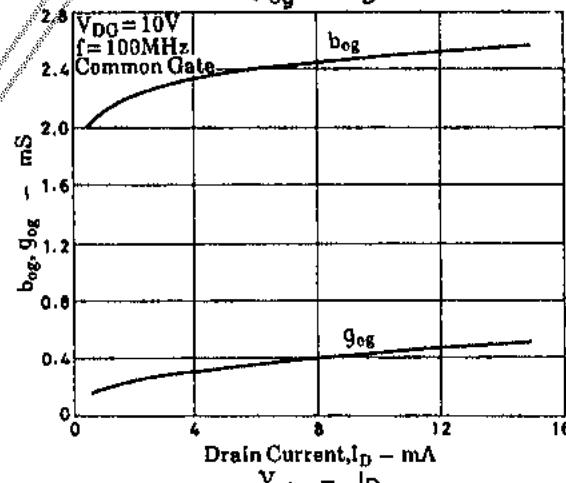
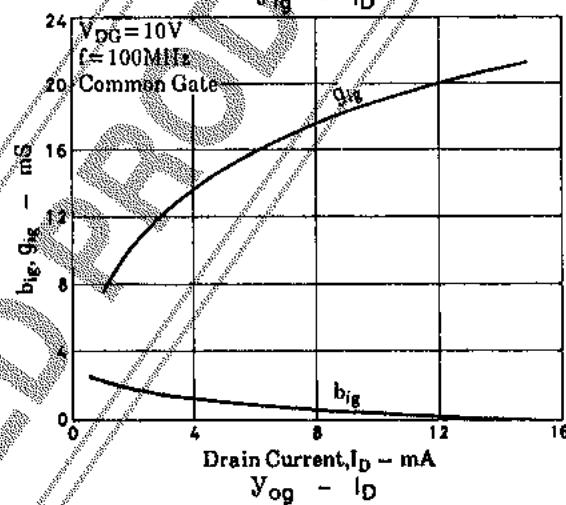
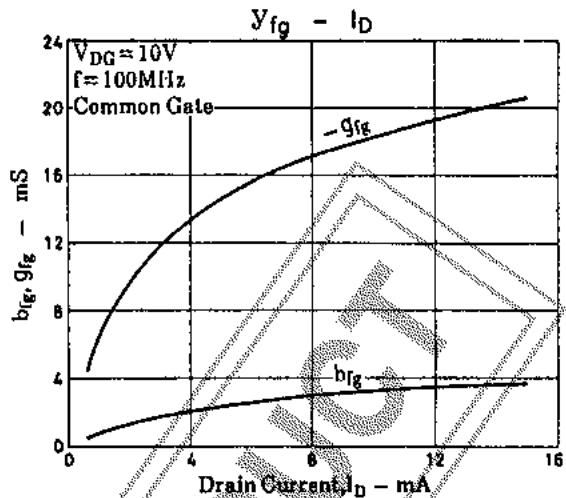
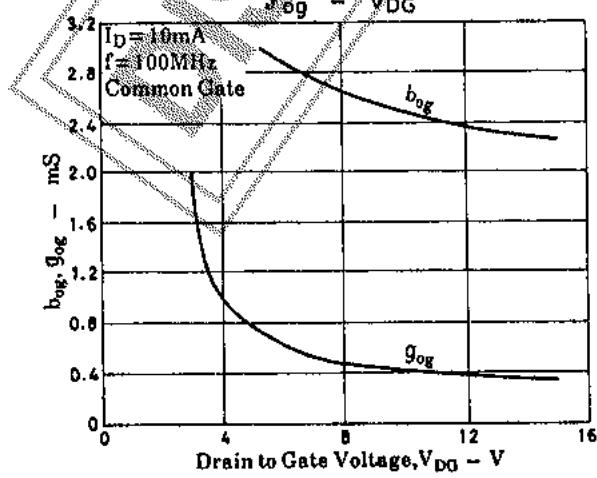
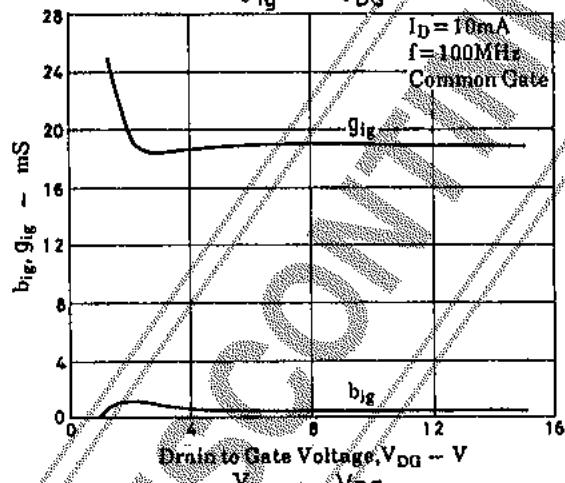
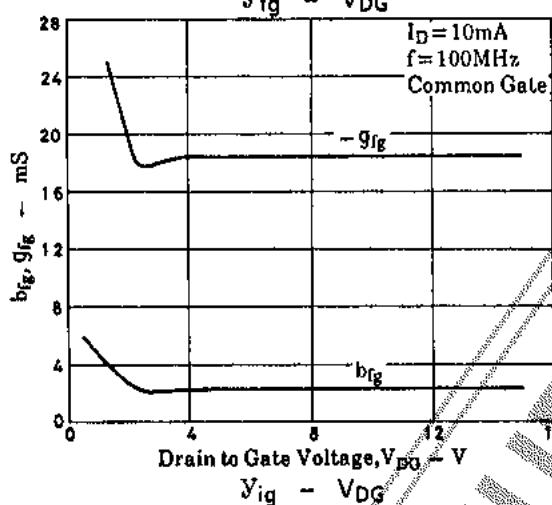
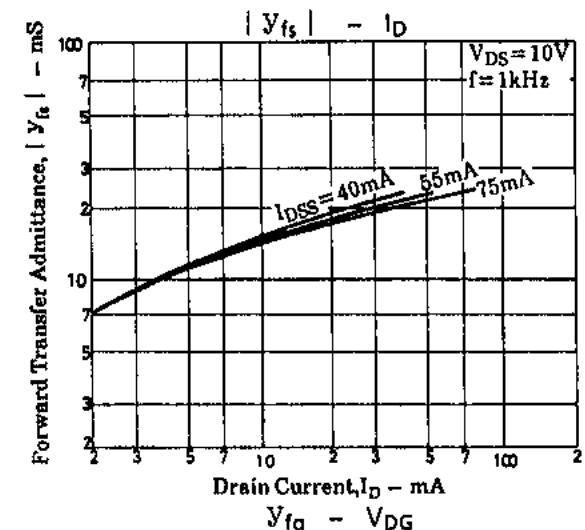
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Package Dimensions 2027A**Package Dimensions 2028A**

Specifications and information herein are subject to change without notice.

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